











TS3A4741, TS3A4742

SCDS228F - AUGUST 2006 - REVISED DECEMBER 2015

TS3A474x 0.9-Ω Low-Voltage Single-Supply 2-Channel SPST Analog Switches

1 Features

- Low ON-State Resistance (R_{on})
 - 0.9-Ω Max (3-V Supply)
 - 1.5-Ω Max (1.8-V Supply)
- 0.4-Ω Max R_{on} Flatness (3-V Supply)
- 1.6-V to 3.6-V Single-Supply Operation
- Available in SOT-23 and VSSOP Packages
- High Current-Handling Capacity (100 mA Continuous)
- 1.8-V CMOS Logic Compatible (3-V Supply)
- Fast Switching: t_{ON} = 14 ns, t_{OFF} = 9 ns

2 Applications

- Power Routing
- · Battery-Powered Systems
- Audio and Video Signal Routing
- Low-Voltage Data-Acquisition Systems
- · Communications Circuits
- PCMCIA Cards
- Cellular Phones
- Modems
- Hard Drives

3 Description

The TS3A4741 and TS3A4742 are bi-directional, 2-channel single-pole/single-throw (SPST) analog switches with low ON-state resistance (R_{on}), low-voltage, that operate from a single 1.6-V to 3.6-V supply. These devices have fast switching speeds, handle rail-to-rail analog signals, and consume very low quiescent power.

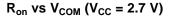
The digital logic input is 1.8-V CMOS compatible when using a single 3-V supply.

The TS3A4741 has two normally open (NO) switches, and the TS3A4742 has two normally closed (NC) switches.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)					
TS3A4741	SOT (8)	2.90 mm × 1.63 mm					
	VSSOP (8)	3.00 mm × 3.00 mm					
TS3A4742	SOT (8)	2.90 mm × 1.63 mm					
	VSSOP (8)	3.00 mm × 3.00 mm					

(1) For all available packages, see the orderable addendum at the end of the datasheet.



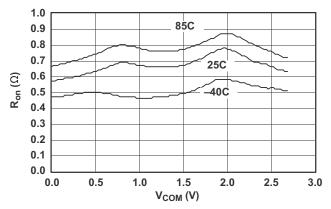




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4 Revision History

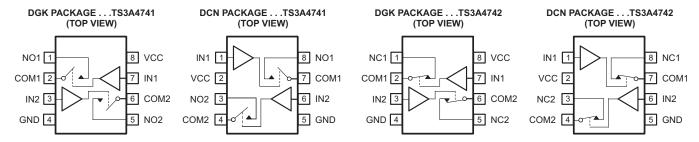
	•	
CI	hanges from Revision E (December 2014) to Revision F	Page
•	Changed DCN package to clarify switch configuration.	3
•	Changed the V _{IN} MAX value in the <i>Recommended Operating Conditions</i> table from: 1.8 V to: V _{CC}	4
CI	hanges from Revision D (June 2014) to Revision E	Page
•	Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical Packaging, and Orderable Information section.	

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5 Pin Configuration and Functions



Pin Functions

		PIN				
NAME	TS3A4	1741	T:	S3A4742	I/O	DESCRIPTION
	MSOP	SOT	MSOP	SOT		
COM1	2	7	2	7	I/O	Common
COM2	6	4	6	4	I/O	Common
GND	4	5	4	5	_	Ground
IN1	7	1	7	1	I	Digital control to connect COM to NO or NC
IN2	3	6	3	6	I	Digital control to connect COM to NO or NC
NC1	_	_	1	8	I/O	Normally closed
NC2	_	_	5	3	I/O	Normally closed
NO1	1	8	_	_	I/O	Normally open
NO2	5	3	_	_	I/O	Normally open
VCC	8	2	8	2	I Power supply	



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage reference to GND ⁽²⁾			4	
$\begin{matrix} V_{NO} \\ V_{COM} \\ V_{IN} \end{matrix}$	Analog and digital voltage		-0.3	V _{CC} + 0.3	V
I _{NO} I _{COM}	On-state switch current	V_{NO} , $V_{COM} = 0$ to V_{CC}	-100	100	
I _{CC} I _{GND}	Continuous current through V_{CC} or GND			±100	mA
	Peak current pulsed at 1 ms, 10% duty cycle	COM, V _{NO} , V _{COM}		±200	
T_A	Operating temperature		-40	85	
T_{J}	Junction temperature			150	°C
T _{stg}	Storage temperature		-65	150	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±4000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage reference to ground	1.6	3.6	V
$V_{NO} \ V_{COM}$	Analog voltage	0	3.6	
V_{COM}				
V _{IN}	Digital Voltage	0	V_{CC}	

6.4 Thermal Information

		TS3A474x		
	THERMAL METRIC ⁽¹⁾	DCN/DGK	UNIT	
		8 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	nce 214.8		
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	191.0		
$R_{\theta JB}$	Junction-to-board thermal resistance	113.1	°C/W	
ΨЈТ	Junction-to-top characterization parameter	52.4		
ΨЈВ	Junction-to-board characterization parameter	110.2		

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

⁽²⁾ Signals on COM or NO exceeding V_{CC} or GND are clamped by internal diodes. Limit forward diode current to maximum current rating.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics (3-V Supply)(1)(2)

 $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$. $T_A = -40 \text{ to } 85^{\circ}\text{C}$. $V_{IH} = 1.4 \text{ V}$. $V_{II} = 0.5 \text{ V}$ (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	TA	MIN	TYP ⁽³⁾	MAX	UNIT
ANALOG SWITC	ж							
V _{COM} , V _{NO} , V _{NC}	Analog signal range				0		V ₊	V
D	ONI state majetana	$V_{CC} = 2.7 \text{ V}, I_{COM} = -10$	00 mA,	25°C		0.7	0.9	
R _{on}	ON-state resistance	V_{NO} , $V_{NC} = 1.5 \text{ V}$		Full			1.1	Ω
ΛD	ON-state resistance match between	$V_{CC} = 2.7 \text{ V}, I_{COM} = -10$	00 mA,	25°C		0.03	0.05	0
ΔR_{on}	channels (4)	$V_{NO}, V_{NC} = 1.5 \text{ V}$		Full			0.15	Ω
D	ON-state resistance flatness ⁽⁵⁾	$V_{CC} = 2.7 \text{ V}, I_{COM} = -10$	00 mA,	25°C		0.23	0.4	Ω
R _{on(flat)}	ON-State resistance nativess V	V_{NO} , $V_{NC} = 1 \text{ V}$, 1.5 V, 2	2 V	Full			0.5	12
L	NO	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0.3$	3 V, 3 V,	25°C	-2	1	2	nA
I _{NO(OFF)}	OFF leakage current ⁽⁶⁾	$V_{NO} = 3 \text{ V}, 0.3 \text{ V}$	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0.3 \text{ V}, 3 \text{ V}, V_{NO} = 3 \text{ V}, 0.3 \text{ V}$		-18		18	IIA
l	COM	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0.3$	3 V, 3 V,	25°C	-2	1	2	nA
ICOM(OFF)	OFF leakage current ⁽⁶⁾	$V_{NO} = 3 \text{ V}, 0.3 \text{ V}$		Full	-18		18	шл
laaa.s	COM	$V_{CC} = 3.6 \text{ V}, V_{COM} = 0.3$		25°C	-2.5	0.01	2.5	nA
ICOM(ON)	ON leakage current ⁽⁶⁾	$V_{NO} = 0.3 \text{ V}, 3 \text{ V}, \text{ or float}$	ting	Full	– 5		5	IIA
DYNAMIC								
t	Turn-on time	$V_{NO}, V_{NC} = 1.5 \text{ V}, R_{L} = 1.5 \text{ V}$	50 Ω,	25°C		5	14	ne
t _{ON}	Turr-ori time	C _L = 35 pF, See Figure 14		Full			15	ns
4	Turn-off time	$V_{NO}, V_{NC} = 1.5 \text{ V}, R_L = 50 \Omega,$ $C_L = 35 \text{ pF}, \text{ See Figure 14}$		25°C		4	9	no
toff				Full			10	ns
Q_C	Charge injection	V _{GEN} = 0, R _{GEN} = 0, C _L = 1 nF, See Figure 15		25°C		3		рC
C _{NO(OFF)}	NO OFF capacitance	f = 1 MHz, See Figure 16	6	25°C		23		
C _{COM(OFF)}	COM OFF capacitance	f = 1 MHz, See Figure 16	6	25°C		20		pF
C _{COM(ON)}	COM ON capacitance	f = 1 MHz, See Figure 16	6	25°C		43		
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON		25°C		125		MHz
0	OFF isolation ⁽⁷⁾	$R_L = 50 \Omega, C_L = 5 pF,$	f = 10 MHz	25.0		-40		٩D
O _{ISO}	OFF ISOIALION**	See Figure 17 f = 1	f = 1	25°C		-62		dB
		MHz						
		D 5000 5 pc	f = 10 MHz			-73		
X _{TALK}	Crosstalk	$R_L = 50 \Omega$, $C_L = 5 pF$, See Figure 17	f = 1	25°C				dB
			MHz			- 95		
			R _L = 32 Ω			0.04%		
THD	Total harmonic distortion	f = 20 Hz to 20 kHz, $V_{COM} = 2 V_{P-P}$		25°C				
		VCOM = Z VP-P	$R_L = 600$ Ω			0.003%		
DIGITAL CONTR	ROL INPUTS (IN1, IN2)		II.	ı l				
V _{IH}	Input logic high			Full	1.4			
V _{IL}	Input logic low			Full			0.5	V
	· · ·	., .		25°C		0.5	1	
I _{IN}	Input leakage current	$V_I = 0$ or V_{CC}		Full	-20		20	nA
SUPPLY		-1		<u> </u>				

- (1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- Parts are tested at 85°C and specified by design and correlation over the full temperature range.
- (3) Typical values are at $V_{CC} = 3 \text{ V}$, $T_A = 25 ^{\circ}\text{C}$.
- $\Delta R_{on} = R_{on(max)} R_{on(min)}$ Flatness is defined as the difference between the maximum and minimum value of r_{on} as measured over the specified analog signal
- Leakage parameters are 100% tested at the maximum-rated hot operating temperature and specified by correlation at $T_A = 25$ °C. OFF isolation = $20_{log}10$ (V_{COM}/V_{NO}), V_{COM} = output, V_{NO} = input to OFF switch



Electrical Characteristics (3-V Supply)⁽¹⁾⁽²⁾ (continued)

 V_{CC} = 2.7 V to 3.6 V, T_A = -40 to 85°C, V_{IH} = 1.4 V, V_{IL} = 0.5 V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TA	MIN	TYP ⁽³⁾ MAX	UNIT
V_{CC}	Power-supply range			2.7	3.6	٧
	Desitive europhy europa	V 26 V V 0 0 7 V	25°C		0.075	
ICC	Positive-supply current	$V_{CC} = 3.6 \text{ V}, V_{IN} = 0 \text{ or } V_{CC}$	Full		0.75	μΑ



6.6 Electrical Characteristics (1.8-V Supply)(1) (2)

 $V_{cc} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40 \text{ to } 85^{\circ}\text{C}$, $V_{IJ} = 1 \text{ V}$, $V_{IJ} = 0.4 \text{ V}$ (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	T _A	MIN	TYP ⁽²⁾	MAX	UNIT
ANALOG SV	WITCH			, ,				
V _{COM} , V _{NO} , V _{NC}	Analog signal range				0		V ₊	V
R _{on}	ON-state resistance	$V_{CC} = 1.8 \text{ V}, I_{COM} = -10 \text{ V}_{NO}, V_{NC} = 0.9 \text{ V}$	0 mA,	25 °C Full		1	1.5	Ω
ΔR _{on}	ON-state resistance match between channels ⁽¹⁾	$V_{CC} = 1.8 \text{ V}, I_{COM} = -10$	0 mA,	25 °C		0.09	0.15	Ω
	ON-state resistance flatness (3)	$V_{NO}, V_{NC} = 0.9 \text{ V}$ $V_{CC} = 1.8 \text{ V}, I_{COM} = -10 \text{ V}$	0 mA,	Full 25 °C		0.7	0.25	Ω
R _{on(flat)}	ON-State resistance natiress ($0 \le V_{NO}, V_{NC} \le V_{CC}$		Full			1.5	12
I _{NO(OFF)}	NO OFF leakage current ⁽⁴⁾	$V_{CC} = 1.95 \text{ V}, V_{COM} = 0$ $V_{NO} = 1.8 \text{ V}, 0.15 \text{ V}$	0.15 V, 1.65 V,	25 °C Full	-1 -10	0.5	10	nA
I _{COM(OFF)}	COM OFF leakage current ⁽⁴⁾	V _{CC} = 1.95 V, V _{COM} = 0 V _{NO} , = 1.8 V, 0.15 V	0.15 V, 1.65 V,	25 °C Full	-1 -10	0.5	1	nA
I _{COM(ON)}	COM ON leakage current ⁽⁴⁾	$V_{CC} = 1.95 \text{ V}, V_{COM} = 0.000 \text{ V}$ $V_{NO} = 0.15 \text{ V}, 1.65 \text{ V}, 0.000 \text{ V}$		25 °C	-1	0.01	1	nA
. ,	ON leakage culterit	V _{NO} = 0.13 V, 1.03 V, 0	i iloating	Full	-3		3	
t _{ON}	Turn-on time	V _{NO} , V _{NC} = 1.5 V, R _L =	50 Ω,	25 °C		6	18	ns
t _{OFF}	Turn-off time	$C_L = 35 \text{ pF}$, See Figure V_{NO} , $V_{NC} = 1.5 \text{ V}$, $R_L =$	50 Ω,	Full 25 °C		5	20 10	ns
WFF	rum on une	C _L = 35 pF, See Figure 14		Full			12	113
Q _C	Charge injection	V _{GEN} = 0, R _{GEN} = 0, C _L See Figure 15	= 1 nF,	25 °C		3.2		рC
C _{NO(OFF)}	NO OFF capacitance	f = 1 MHz, See Figure 1		25 °C		23		-
C _{COM(OFF)}	COM OFF capacitance	f = 1 MHz, See Figure 1		25 °C		20		pF
C _{COM(ON)}	COM ON capacitance	f = 1 MHz, See Figure 1	6	25 °C		43		
BW	Bandwidth	$R_L = 50 \Omega$, Switch ON		25 °C		123		MHz
O _{ISO}	OFF isolation ⁽⁵⁾	$R_L = 50 \Omega$, $C_L = 5 pF$, See Figure 17	f = 10 MHz f = 100 MHz	25 °C		-61 -36		dB
X _{TALK}	Crosstalk	$R_L = 50 \Omega$, $C_L = 5 pF$, See Figure 17	f = 10 MHz f = 100 MHz	25 °C		-95 -73		dB
THD	Total harmonic distortion	f = 20 Hz to 20 kHz, V _{COM} = 2 V _{P-P}	$R_L = 32 \Omega$ $R_I = 600 \Omega$	25 °C		0.14%		
DIGITAL CO	ONTROL INPUTS (IN1, IN2)		· ·L					
V _{IH}	Input logic high			Full	1			
V _{IL}	Input logic low			Full			0.4	V
I _{IN}	Input leakage current	V _I = 0 or V _{CC}		25 °C Full	-10	0.1	5 10	nA
SUPPLY		l		-				<u> </u>
V _{CC}	Power-supply range				1.65		1.95	V
I _{CC}	Positive-supply current	V _I = 0 or V _{CC}		25 °C Full			0.05	μΑ

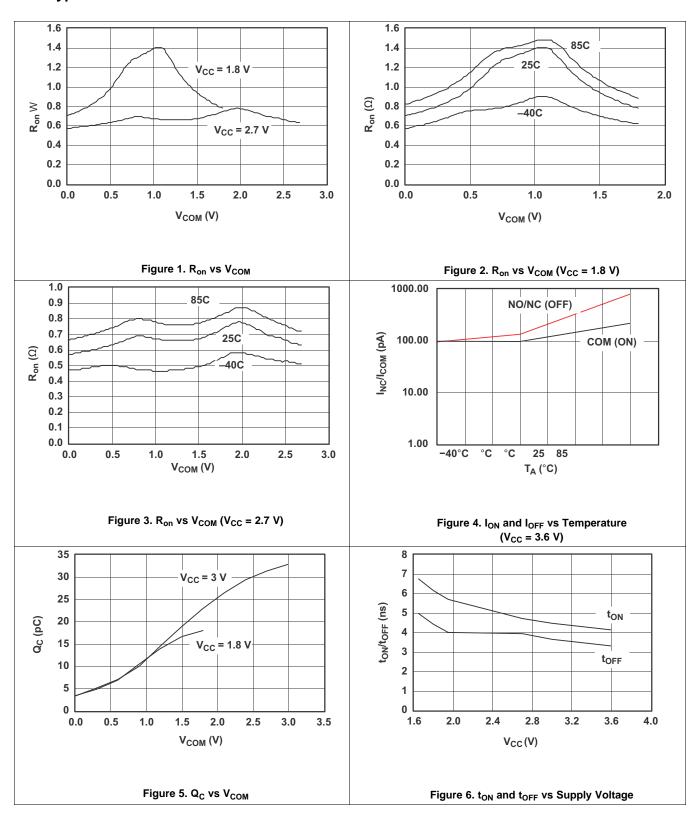
 ⁽¹⁾ ΔR_{on} = R_{on(max)} - R_{on(min)}
 (2) Typical values are at T_A = 25°C.
 (3) Flatness is defined as the difference between the maximum and minimum value of r_{on} as measured over the specified analog signal

Leakage parameters are 100% tested at the maximum-rated hot operating temperature and specified by correlation at T_A = 25°C.

OFF isolation = $20_{log}10$ (V_{COM}/V_{NO}), V_{COM} = output, V_{NO} = input to OFF switch

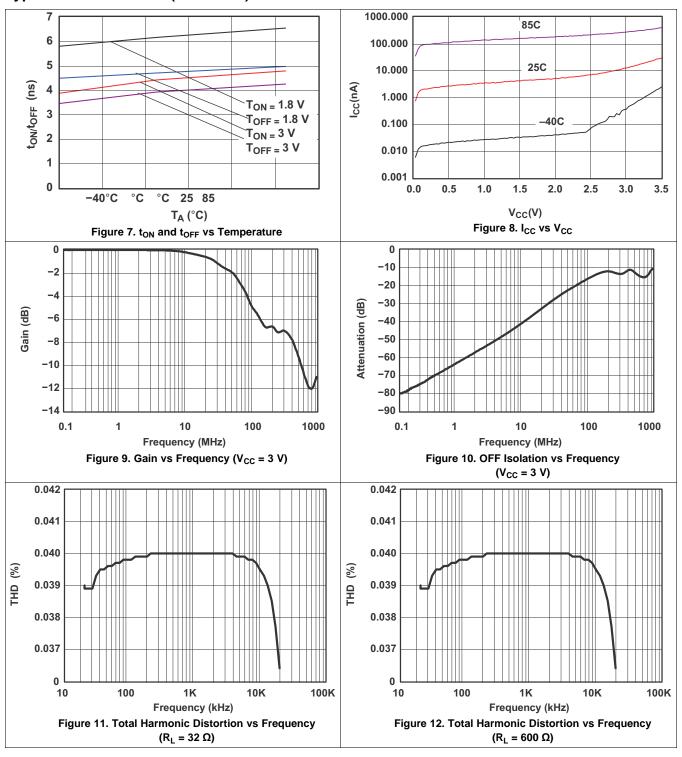


6.7 Typical Characteristics



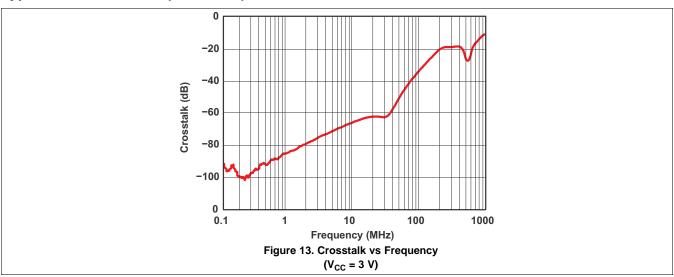


Typical Characteristics (continued)





Typical Characteristics (continued)



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7 Parameter Measurement Information

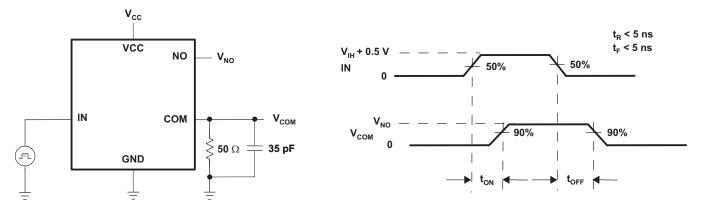
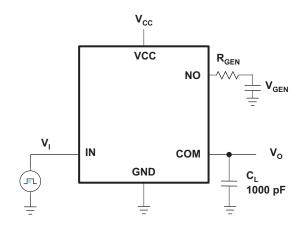


Figure 14. Switching Times



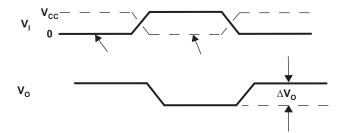


Figure 15. Charge Injection (Q_C)



Parameter Measurement Information (continued)

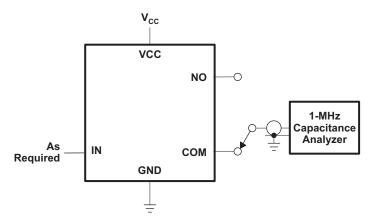
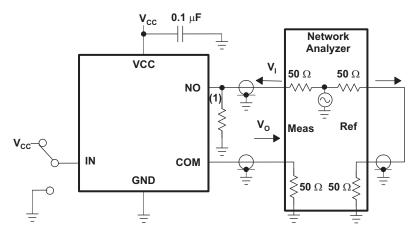


Figure 16. NO and COM Capacitance



Measurements are standardized against short at socket terminals. OFF isolation is measured between COM and OFF terminals on each switch. Bandwidth is measured between content of terminals on each switch. Signal (1) Add 50-Ω termination for the content of the content direction through switch is reversed; worst values are recorded.

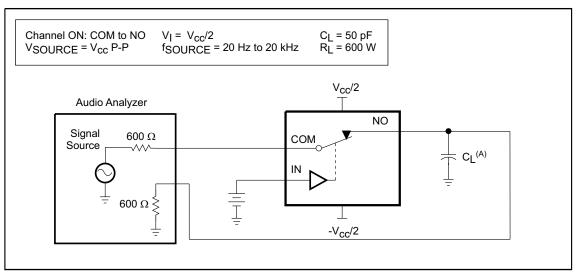
OFF isolation = 20 $\log V_0/V_1$

OFF isolation

Figure 17. OFF Isolation, Bandwidth, and Crosstalk



Parameter Measurement Information (continued)



A. C_L includes probe and jig capacitance.

Figure 18. Total Harmonic Distortion (THD)



8 Detailed Description

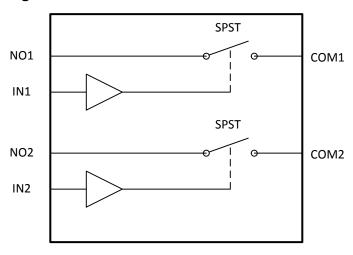
8.1 Overview

The TS3A4741 and TS3A4742 are bi-directional, 2-channel single-pole/single-throw (SPST) analog switches with low ON-state resistance (R_{on}), low-voltage, that operate from a single 1.6-V to 3.6-V supply. These devices have fast switching speeds, handle rail-to-rail analog signals, and consume very low quiescent power.

The digital logic input is 1.8-V CMOS compatible when using a single 3-V supply.

The TS3A4741 has two normally open (NO) switches, and the TS3A4742 has two normally closed (NC) switches.

8.2 Functional Block Diagram



8.3 Feature Description

The TS3A4741 and TS3A4742 has a low on resistance and high current handling capability up to 100 mA continuous current so it can be used for power sequencing and routing with minimal losses. The switch is also bidirectional with fast switching times in the 10 ns range which allows data acquisition and communication between multiple devices.

With a 3-V supply these devices are compatible with standard 1.8-V CMOS logic.

8.4 Device Functional Modes

Table 1. Function Table

IN	NO to COM, COM to NO (TS3A4741)	NC to COM, COM to NC (TS3A4742)
L	OFF	ON
Н	ON	OFF



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Analog signals that range over the entire supply voltage (V_{CC} to GND) of the TS3A4741 and TS3A4742 can be passed with very little change in R_{on} (see *Typical Characteristics*). The switches are bidirectional, so the NO, NC, and COM pins can be used as either inputs or outputs.

9.2 Typical Application

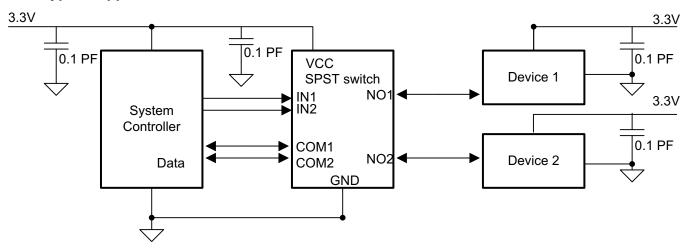


Figure 19. Typical Application Schematic

9.2.1 Design Requirements

Ensure that all of the signals passing through the switch are within the specified ranges to ensure proper performance.

9.2.2 Detailed Design Procedure

The TS3A474x can be properly operated without any external components. However, TI recommends that unused pins should be connected to ground through a $50-\Omega$ resistor to prevent signal reflections back into the device. TI also recommends that the digital control pins (INx) be pulled up to V_{CC} or down to GND to avoid undesired switch positions that could result from the floating pin.



Typical Application (continued)

9.2.3 Application Curve

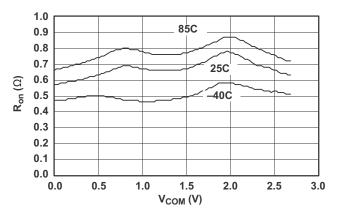


Figure 20. R_{on} vs V_{COM} (V_{CC} = 2.7 V)



10 Power Supply Recommendations

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings, because stresses beyond the listed ratings can cause permanent damage to the device. Always sequence VCC on first, followed by NO, NC, or COM.

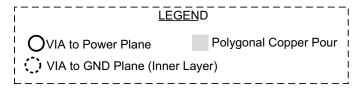
Although it is not required, power-supply bypassing improves noise margin and prevents switching noise propagation from the VCC supply to other components. A $0.1-\mu F$ capacitor, connected from VCC to GND, is adequate for most applications.

11 Layout

11.1 Layout Guidelines

High-speed switches require proper layout and design procedures for optimum performance. Reduce stray inductance and capacitance by keeping traces short and wide. Ensure that bypass capacitors are as close to the device as possible. Use large ground planes where possible.

11.2 Layout Example



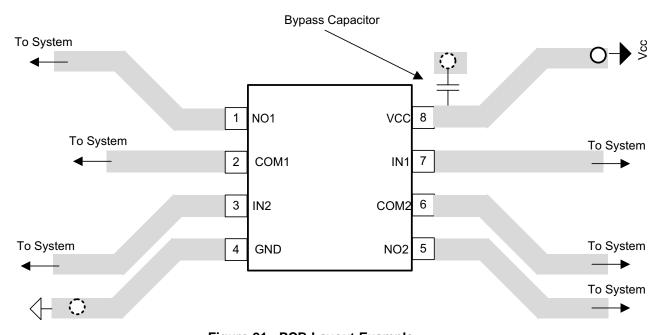


Figure 21. PCB Layout Example



12 Device and Documentation Support

12.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 2. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY	
TS3A4741	Click here	Click here	Click here	Click here	Click here	
TS3A4742	Click here	Click here	Click here	Click here	Click here	

12.2 Trademarks

All trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
TS3A4741DCNR	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(8BLO, 8BLR)
TS3A4741DCNR.B	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(8BLO, 8BLR)
TS3A4741DCNRG4	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8BLR
TS3A4741DCNRG4.B	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8BLR
TS3A4741DGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	JYR
TS3A4741DGKR.B	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	JYR
TS3A4742DCNR	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(8BPO, 8BPR)
TS3A4742DCNR.B	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(8BPO, 8BPR)
TS3A4742DCNRG4	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8BPR
TS3A4742DCNRG4.B	Active	Production	SOT-23 (DCN) 8	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	8BPR
TS3A4742DGKR	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	L7R
TS3A4742DGKR.B	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	L7R

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No. RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS3A4741DCNR	SOT-23	DCN	8	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS3A4741DCNRG4	SOT-23	DCN	8	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS3A4741DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS3A4742DCNR	SOT-23	DCN	8	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS3A4742DCNRG4	SOT-23	DCN	8	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS3A4742DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS3A4741DCNR	SOT-23	DCN	8	3000	202.0	201.0	28.0
TS3A4741DCNRG4	SOT-23	DCN	8	3000	202.0	201.0	28.0
TS3A4741DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
TS3A4742DCNR	SOT-23	DCN	8	3000	202.0	201.0	28.0
TS3A4742DCNRG4	SOT-23	DCN	8	3000	202.0	201.0	28.0
TS3A4742DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0

DCN (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Package outline exclusive of metal burr & dambar protrusion/intrusion.
- D. Package outline inclusive of solder plating.
- E. A visual index feature must be located within the Pin 1 index area.
- F. Falls within JEDEC MO-178 Variation BA.
- G. Body dimensions do not include flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.



DCN (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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